

Silicon NPN Power Transistors

2SC2899

DESCRIPTION

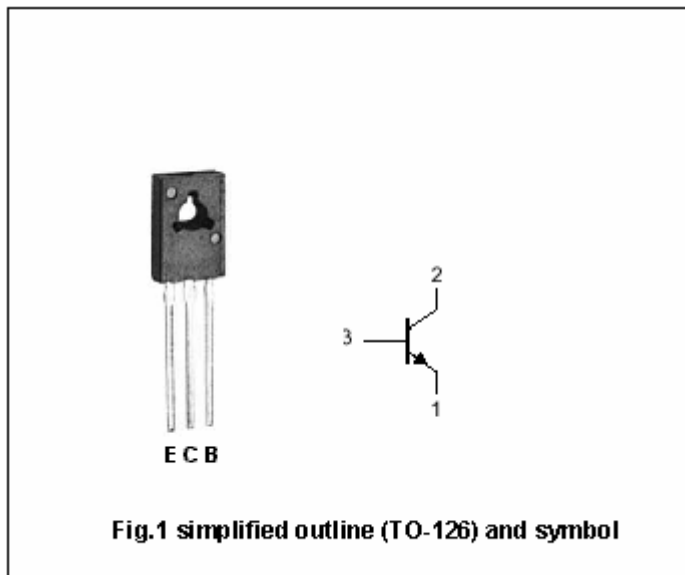
- With TO-126 package
- High voltage,high speed

APPLICATIONS

- For high speed and high voltage switching applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | Emitter     |
| 2   | Collector   |
| 3   | Base        |



Absolute maximum ratings (Ta=25°C)

| SYMBOL           | PARAMETER                   | CONDITIONS           | VALUE   | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V <sub>CBO</sub> | Collector-base voltage      | Open emitter         | 500     | V    |
| V <sub>CEO</sub> | Collector-emitter voltage   | Open base            | 400     | V    |
| V <sub>EBO</sub> | Emitter-base voltage        | Open collector       | 10      | V    |
| I <sub>C</sub>   | Collector current           |                      | 0.5     | A    |
| I <sub>CM</sub>  | Collector current-peak      |                      | 1.0     | A    |
| P <sub>C</sub>   | Collector power dissipation | T <sub>a</sub> =25°C | 0.75    | W    |
|                  |                             | T <sub>C</sub> =25°C | 10      |      |
| T <sub>j</sub>   | Junction temperature        |                      | 150     | °C   |
| T <sub>stg</sub> | Storage temperature         |                      | -55~150 | °C   |

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

| SYMBOL                | PARAMETER                            | CONDITIONS  | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V <sub>CEO(SUS)</sub> | Collector-emitter sustaining voltage | I <sub>C</sub> =0.1A; R <sub>BE</sub> =∞, L=100mH | 400 |      |     | V    |
| V <sub>(BR)EBO</sub>  | Emitter-base breakdown voltage       | I <sub>E</sub> =10mA; I <sub>C</sub> =0           | 10  |      |     | V    |
| V <sub>CEsat</sub>    | Collector-emitter saturation voltage | I <sub>C</sub> =250mA; I <sub>B</sub> =50m A      |     |      | 1.0 | V    |
| V <sub>BEsat</sub>    | Base-emitter saturation voltage      | I <sub>C</sub> =250mA ; I <sub>B</sub> =50m A     |     |      | 1.5 | V    |
| h <sub>FE-1</sub>     | DC current gain                      | I <sub>C</sub> =250mA ; V <sub>CE</sub> =5V       | 15  |      |     |      |
| h <sub>FE-2</sub>     | DC current gain                      | I <sub>C</sub> =500mA ; V <sub>CE</sub> =5V       | 7   |      |     |      |
| I <sub>CBO</sub>      | Collector cut-off current            | V <sub>CB</sub> =400V; I <sub>E</sub> =0          |     |      | 20  | μA   |
| I <sub>CEO</sub>      | Collector cut-off current            | V <sub>CE</sub> =350V; R <sub>BE</sub> =∞         |     |      | 50  | μA   |

## Switching times

|                  |              |  |  |  |     |    |
|------------------|--------------|--|--|--|-----|----|
| t <sub>on</sub>  | Turn-on time | I <sub>C</sub> =0.5A; I <sub>B1</sub> =-I <sub>B2</sub> =0.1A<br>V <sub>CC</sub> ≈150V |  |  | 1.0 | μs |
| t <sub>stg</sub> | Storage time |  |  |  | 2.0 | μs |
| t <sub>f</sub>   | Fall time    |  |  |  | 1.0 | μs |

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PACKAGE OUTLINE

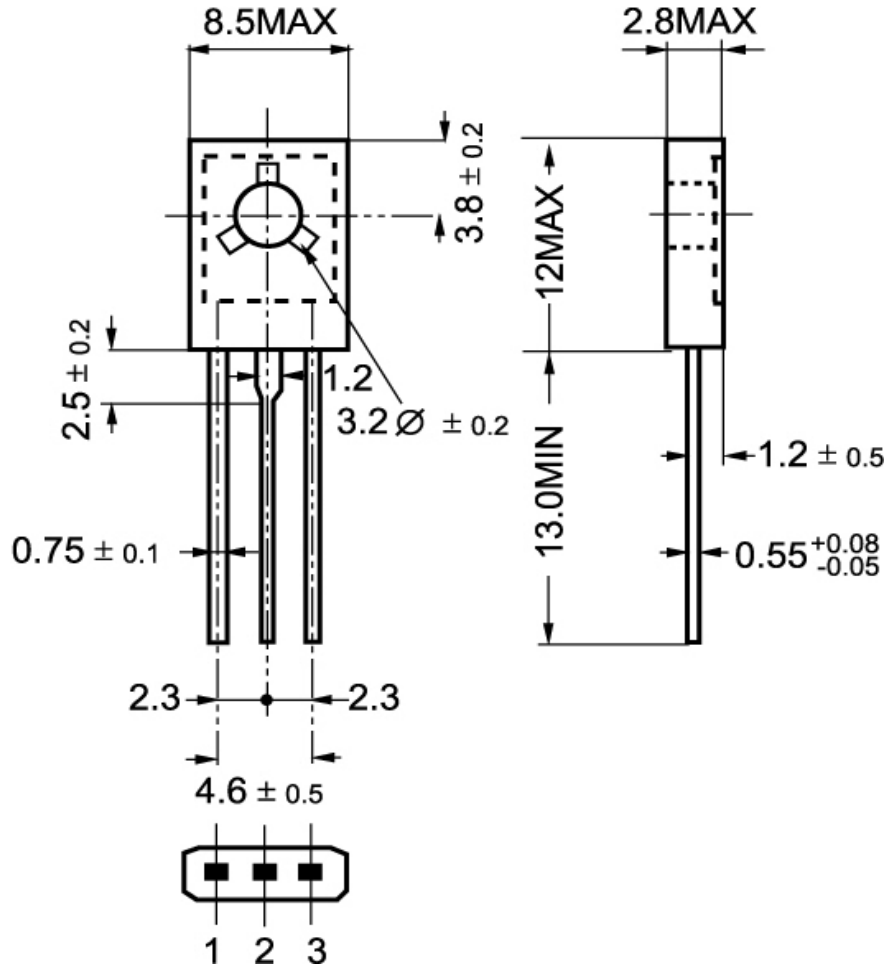


Fig.2 outline dimensions

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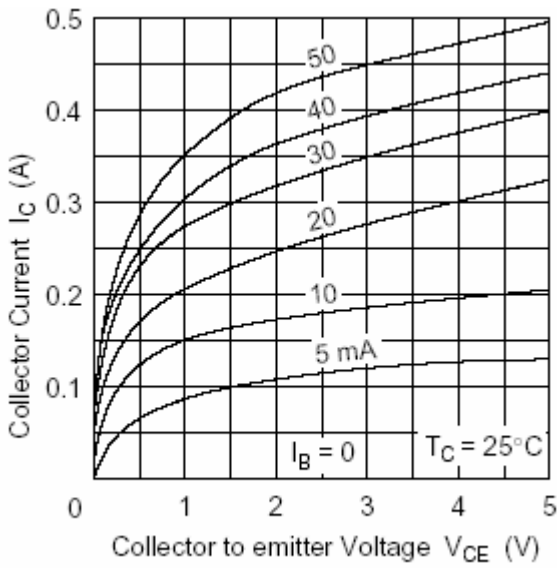


Fig.3 Static Characteristic

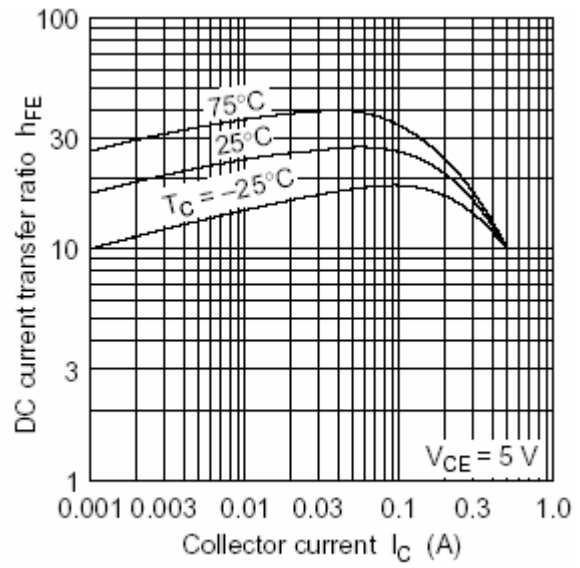


Fig.4 DC current Gain

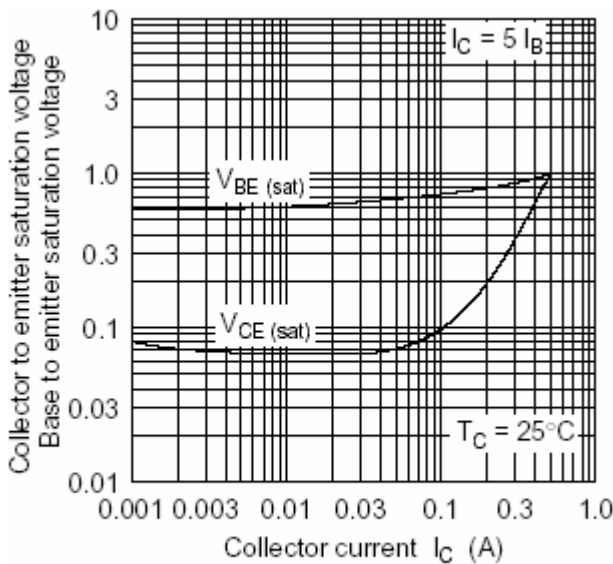


Fig.5 Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

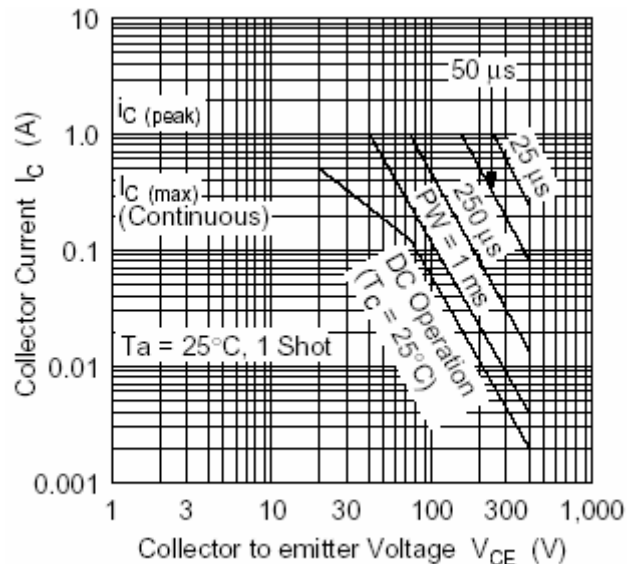


Fig.6 Safe Operating Area